

Interference Search

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	702	semiconductor laser diode.clm.	US-PGPUB; USPAT	ADJ	OFF	2006/08/05 13:27
L2	2804	(GaN or InGaN GaInN or AlGaN GaAlN or InAlGaN GaAlInN GaInAlN).clm.	US-PGPUB; USPAT	ADJ	OFF	2006/08/05 13:30
L5	3058	(GaN or InGaN GaInN or AlGaN GaAlN or InAlGaN GaAlInN GaInAlN).clm.	US-PGPUB; USPAT	OR	OFF	2006/08/05 13:31
L6	13	1 with 5	US-PGPUB; USPAT	OR	OFF	2006/08/05 13:31
L7	22	1 and 5	US-PGPUB; USPAT	OR	OFF	2006/08/05 13:31
L8	1822	(Gallium Nitride or Indium Gallium Nitride or Gallium Indium Nitride or Aluminum Gallium Nitride Gallium Aluminum Nitride or Indium Aluminum Gallium Nitride or Gallium Aluminum Indium Nitride or Gallium Indium Aluminum Nitride).clm.	US-PGPUB; USPAT	ADJ	ON	2006/08/05 13:35
L9	4310	5 or 8	US-PGPUB; USPAT	ADJ	ON	2006/08/05 13:35
L13	8985	(AL aluminum) near2 (content composition percent percentage amount).clm.	US-PGPUB; USPAT	OR	ON	2006/08/05 13:38
L14	72	9 with 13	US-PGPUB; USPAT	ADJ	ON	2006/08/05 13:38
L15	157	9 and 13	US-PGPUB; USPAT	ADJ	ON	2006/08/05 13:38
L16	1	1 and 14	US-PGPUB; USPAT	ADJ	ON	2006/08/05 13:38
L17	3	1 and 15	US-PGPUB; USPAT	ADJ	ON	2006/08/05 13:38